



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

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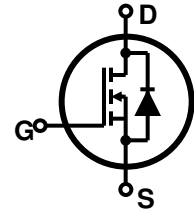
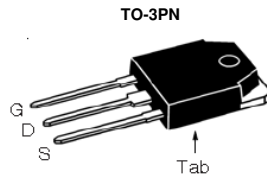


N-channel MOSFET

Features

- Low gate charge
- 100% avalanche tested
- Improved dv/dt capability
- RoHS compliant
- JEDEC Qualification

BV_{DSS}	I_D	$R_{DS(on)}$
900V	9.5A	< 1.4 Ω



Device	Package	Marking	Remark
GP1M009A090N	TO-3PN	GP1M009A090N	RoHS

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	900	V
Gate-Source Voltage	V_{GS}	± 30	V
Continuous Drain Current	I_D	$T_C = 25\text{ }^\circ\text{C}$	9.5
		$T_C = 100\text{ }^\circ\text{C}$	5.9
Pulsed Drain Current (Note 1)	I_{DM}	36	A
Single Pulse Avalanche Energy (Note 2)	E_{AS}	210	mJ
Repetitive Avalanche Current (Note 1)	I_{AR}	9.5	A
Repetitive Avalanche Energy (Note 1)	E_{AR}	31.2	mJ
Power Dissipation	P_D	$T_C = 25\text{ }^\circ\text{C}$	312
		Derate above 25 $^\circ\text{C}$	2.5
Peak Diode Recovery dv/dt (Note 3)	dv/dt	4.5	V/ns
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55~150	$^\circ\text{C}$
Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	T_L	300	$^\circ\text{C}$

* Limited only by maximum junction temperature

Thermal Characteristics

Parameter	Symbol	Value	Unit
Maximum Thermal resistance, Junction to Case	$R_{\theta JC}$	0.4	$^\circ\text{C}/\text{W}$
Typical Thermal resistance, Case to Sink(Typical)	$R_{\theta CS}$	0.24	$^\circ\text{C}/\text{W}$
Maximum Thermal resistance, Junction to Ambient	$R_{\theta JA}$	40	$^\circ\text{C}/\text{W}$

Electrical Characteristics : $T_C=25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Test condition	Min	Typ	Max	Units
OFF						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	900	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 900\text{ V}, V_{GS} = 0\text{ V}$	--	--	10	μA
		$V_{DS} = 720\text{ V}, T_C = 125^\circ\text{C}$	--	--	100	μA
Forward Gate-Source Leakage Current	I_{GSSF}	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
Reverse Gate-Source Leakage Current	I_{GSSR}	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

ON

Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	2	--	4	V
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 4.75\text{ A}$	--	1.13	1.4	Ω
Forward Transconductance ^(Note 4)	g_{FS}	$V_{DS} = 30\text{ V}, I_D = 4.75\text{ A}$	--	10	--	S

DYNAMIC

Input Capacitance	C_{ISS}	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	2324	--	pF
Output Capacitance	C_{OSS}		--	184	--	pF
Reverse Transfer Capacitance	C_{rSS}		--	29	--	pF

SWITCHING

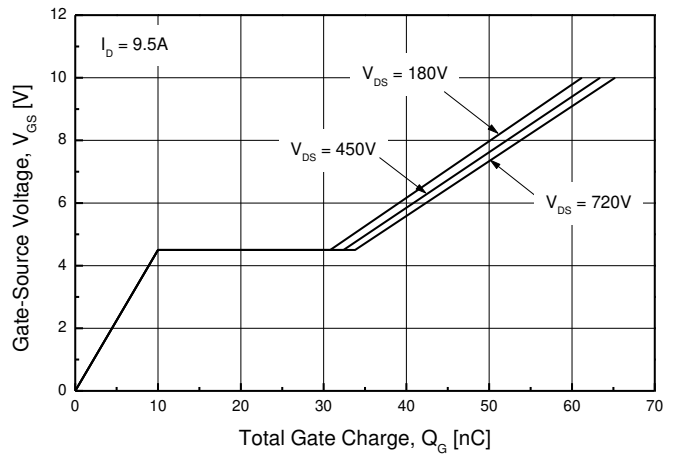
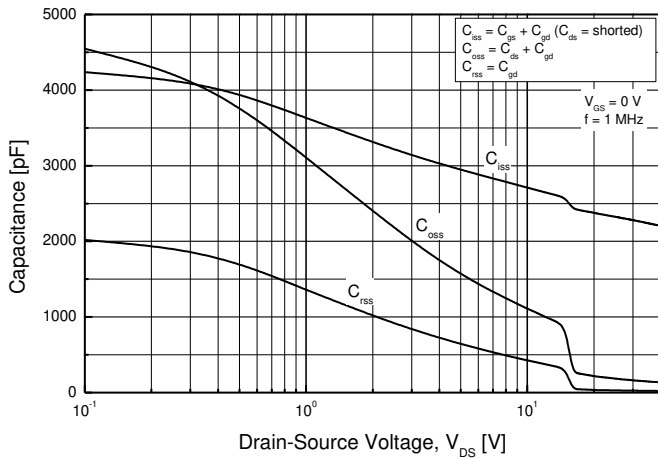
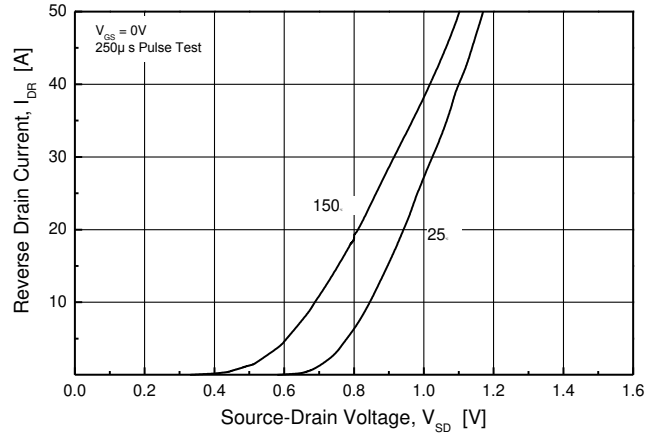
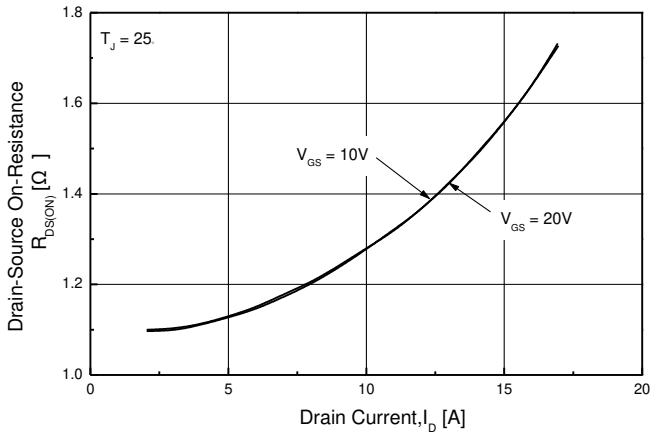
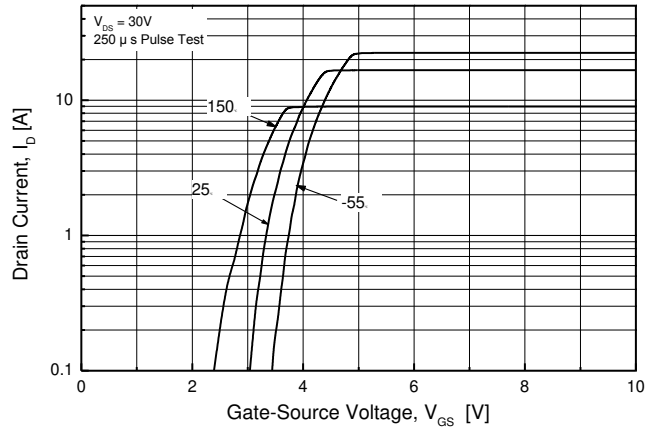
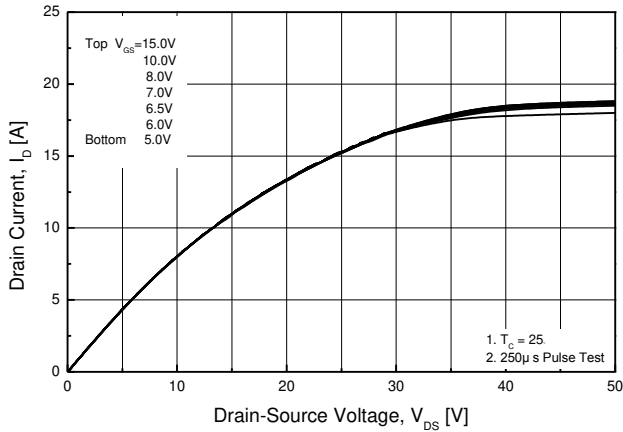
Turn-On Delay Time ^(Note 4,5)	$t_{d(on)}$	$V_{DD} = 450\text{ V}, I_D = 9.5\text{ A},$ $R_G = 25\ \Omega$	--	61	--	ns
Turn-On Rise Time ^(Note 4,5)	t_r		--	49	--	ns
Turn-Off Delay Time ^(Note 4,5)	$t_{d(off)}$		--	318	--	ns
Turn-Off Fall Time ^(Note 4,5)	t_f		--	100	--	ns
Total Gate Charge ^(Note 4,5)	Q_g	$V_{DS} = 720\text{ V}, I_D = 9.5\text{ A},$ $V_{GS} = 10\text{ V}$	--	65	--	nC
Gate-Source Charge ^(Note 4,5)	Q_{gs}		--	11	--	nC
Gate-Drain Charge ^(Note 4,5)	Q_{gd}		--	23	--	nC

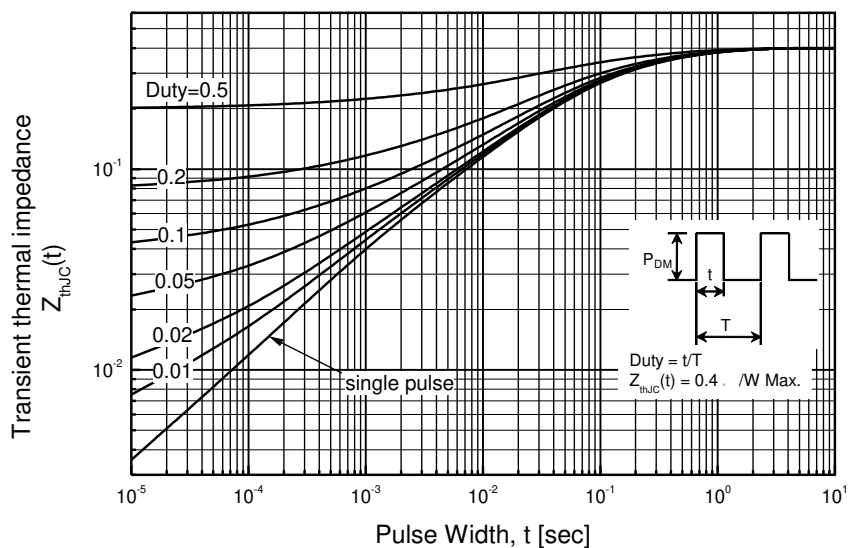
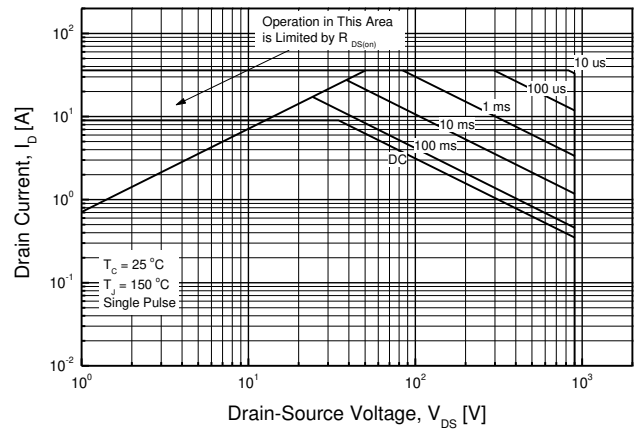
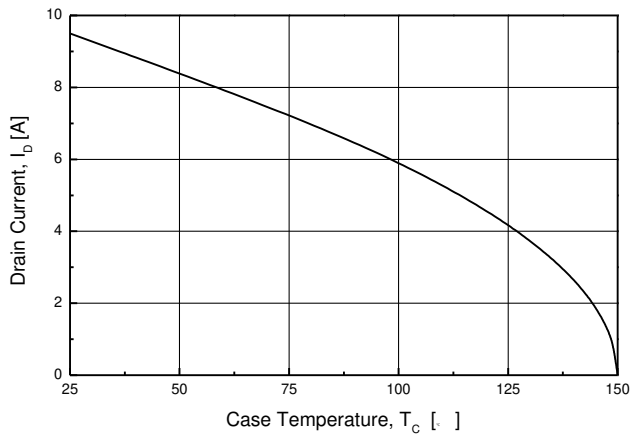
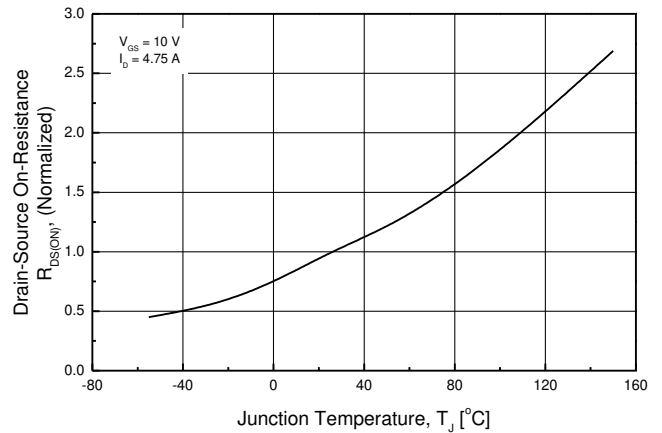
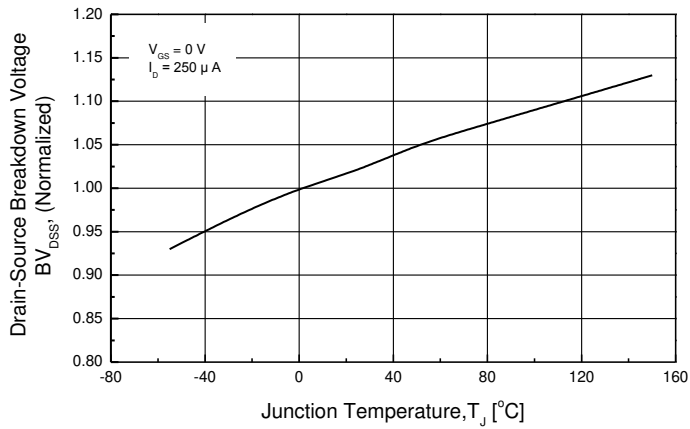
SOURCE DRAIN DIODE

Maximum Continuous Drain-Source Diode Forward Current	I_S	---	--	--	9	A
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}	---	--	--	36	A
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_S = 9.5\text{ A}$	--	--	1.5	V
Reverse Recovery Time ^(Note 4)	t_{rr}	$V_{GS} = 0\text{ V}, I_S = 9.5\text{ A}$ $di_F / dt = 100\text{ A}/\mu\text{s}$	--	469	--	ns
Reverse Recovery Charge ^(Note 4)	Q_{rr}		--	4.9	--	μC

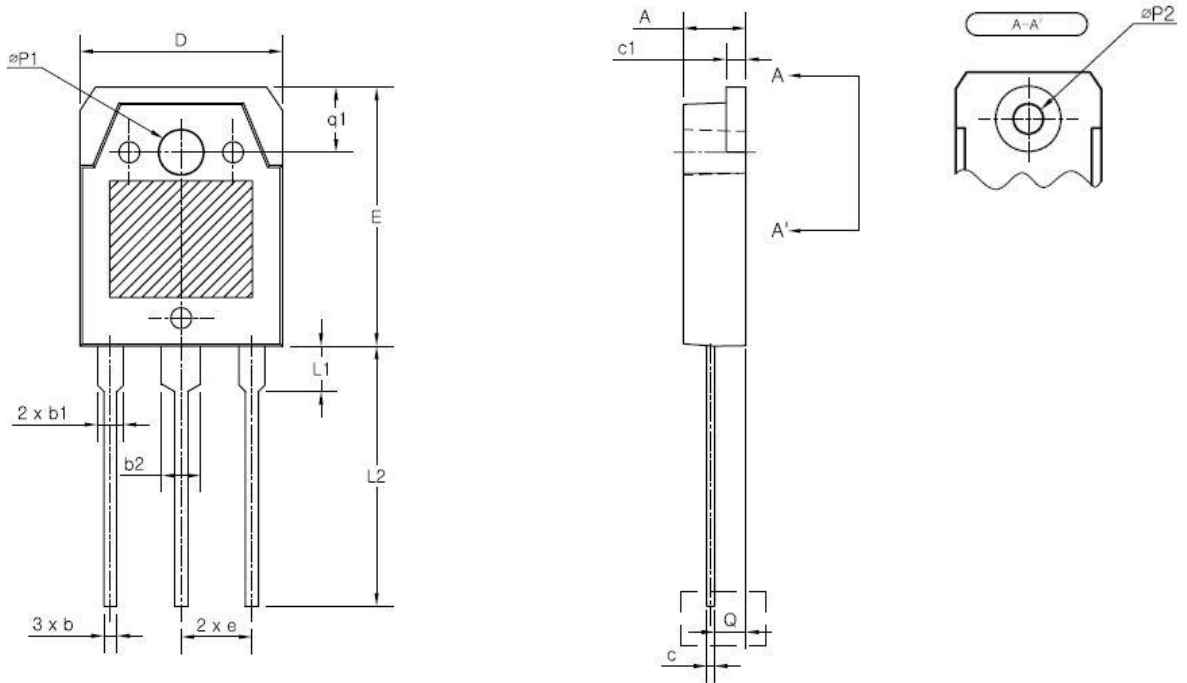
Note :

1. Repeated rating : Pulse width limited by safe operating area
2. $L = 4.4\text{ mH}, I_{AS} = 9.5\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\ \Omega$, Starting $T_J = 25^\circ\text{C}$, not subject to production test – verified by design/characterization
3. $I_{SD} \leq 9.5\text{ A}, di/dt \leq 200\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DS}$, Starting $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2\%$
5. Essentially Independent of Operating Temperature Typical Characteristics





TO-3PN MECHANICAL DATA



SYMBOL	MIN	NOM	MAX
A	4.60	4.80	5.00
b	0.80	1.00	1.20
b1	1.80	2.00	2.20
b2	2.80	3.00	3.20
c	0.55	0.60	0.75
c1	1.45	1.50	1.65
D	15.40	15.60	15.80
E	19.70	19.90	20.10
e	5.15	5.45	5.75
L1	3.30	3.50	3.70
L2	19.80	20.00	20.20
$\varnothing P1$	3.30	3.40	3.50
$\varnothing P2$	(3.20)		
Q	2.20	2.40	2.60
q1	4.80	5.00	5.20

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